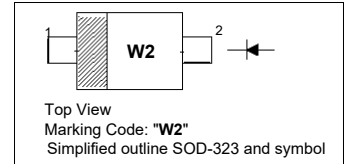


1N914WS Silicon Epitaxial Planar Switching Diode

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

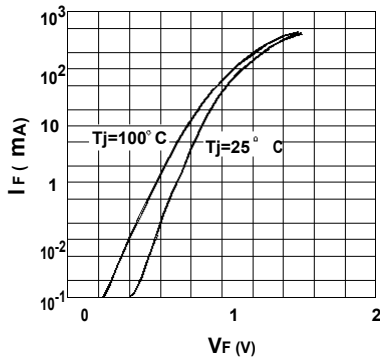
Parameter	Symbol	Value	Unit
Repetitive Reverse Voltage	V_{RRM}	100	V
Average Rectified Forward Current	$I_{F(AV)}$	200	mA
Non-repetitive Peak Forward Surge Current	I_{FSM}	0.5 1	A
Power Dissipation	P_{tot}	200	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	625	$^\circ\text{C/W}$
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Electrical Characteristics ($T_a = 25^\circ\text{C}$)

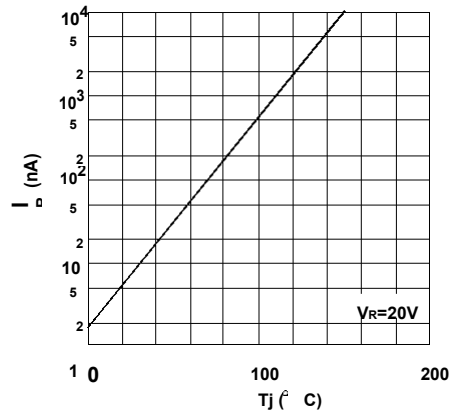
Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 10\text{ mA}$	V_F	-	1	V
Reverse Breakdown Voltage at $I_R = 5\ \mu\text{A}$	$V_{(BR)R}$	75	-	V
Reverse Breakdown Voltage at $I_R = 100\ \mu\text{A}$	$V_{(BR)R}$	100	-	V
Reverse Current at $V_R = 20\text{ V}$	I_R	-	25	nA
Reverse Current at $V_R = 75\text{ V}$		-	5	μA
Reverse Current at $V_R = 20\text{ V}, T_J = 150^\circ\text{C}$		-	50	μA
Total Capacitance at $V_R = 0\text{ V}, f = 1\text{ MHz}$	C_{tot}	-	4	pF
Reverse Recovery Time at $I_F = I_R = 30\text{ mA}, R_L = 100\ \Omega, I_{RR} = 3\text{ mA}$	t_{rr}	-	50	ns

Typical Characteristics

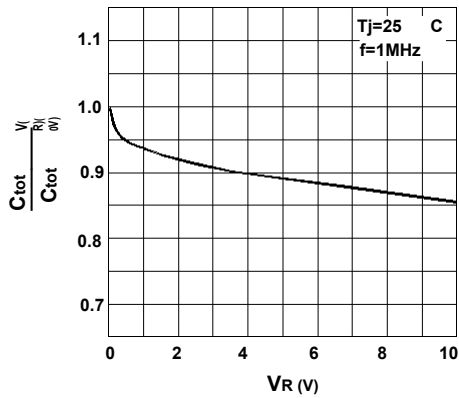
Forward characteristics



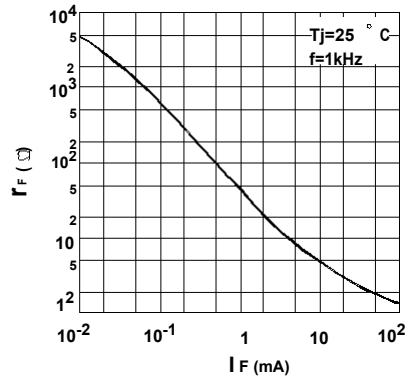
Leakage current vs. junction temperature



Reverse capacitance vs. reverse voltage



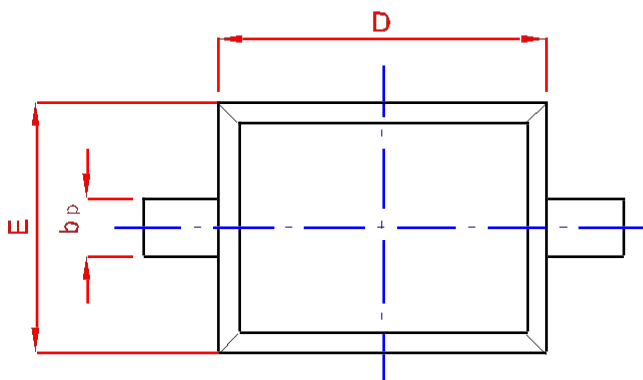
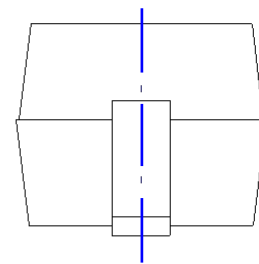
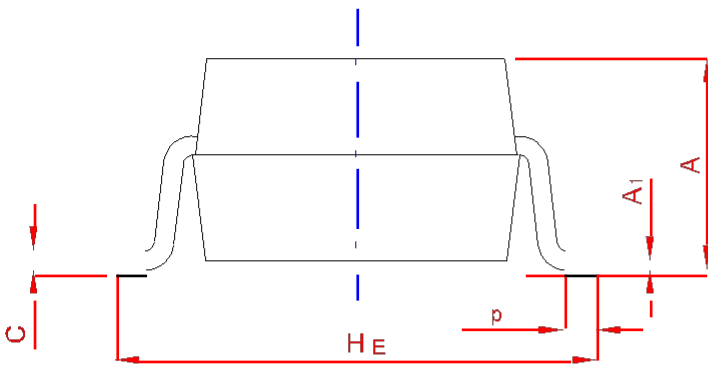
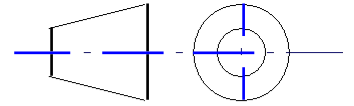
Dynamic forward resistance vs. forward current



PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323



UNIT	A	bp	C	D	E	HE	A1	Lp
mm	1.20	0.40	0.15	1.80	1.35	2.80	0.10	0.50
	0.90	0.25	0.10	1.60	1.15	2.30	0.01	0.20